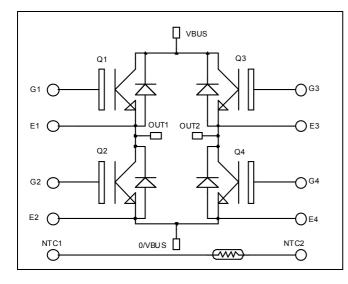
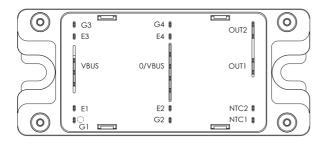


Full - Bridge Trench + Field Stop IGBT3 Power Module





APTGT150H60TG

$V_{CES} = 600V$ $I_{C} = 150A$ @ Tc = 80°C

Application

- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies
- Motor control

Features

- Trench + Field Stop IGBT3 Technology
 - Low voltage drop
 - Low tail current
 - Switching frequency up to 20 kHz
 - Soft recovery parallel diodes
 - Low diode VF
 - Low leakage current
 - RBSOA and SCSOA rated
- Kelvin emitter for easy drive
- Very low stray inductance
 - Symmetrical design
 - Lead frames for power connections
- High level of integration
- Internal thermistor for temperature monitoring

Benefits

- Stable temperature behavior
- Very rugged
- Solderable terminals for easy PCB mounting
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Easy paralleling due to positive TC of VCEsat
- Low profile
- RoHS compliant

Absolute maximum ratings

Symbol	Parameter		Max ratings	Unit
V _{CES}	CES Collector - Emitter Breakdown Voltage I _C Continuous Collector Current CM Pulsed Collector Current V _{GE} Gate – Emitter Voltage P _D Maximum Power Dissipation		600	V
т	Continuous Collector Current	$T_C = 25^{\circ}C$	225	
IC	Continuous Conector Current	$T_C = 80^{\circ}C$	150	А
I _{CM}	Pulsed Collector Current	$T_C = 25^{\circ}C$	350	
V _{GE}	Gate – Emitter Voltage		± 20	V
P _D	Maximum Power Dissipation	$T_C = 25^{\circ}C$	480	W
RBSOA	Reverse Bias Safe Operating Area	$T_{j} = 150^{\circ}C$	300A @ 550V	

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com



All ratings (a) $T_j = 25^{\circ}C$ unless otherwise specified

Electrical Characteristics

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
I _{CES}	Zero Gate Voltage Collector Current	$V_{GE} = 0V, V_{CE} = 600V$				250	μA
V _{CE(sat)}	Collector Emitter Saturation Voltage	VGE 15 V	$T_j = 25^{\circ}C$		1.5	1.9	V
V CE(sat)			$T_{j} = 150^{\circ}C$		1.7		v
V _{GE(th)}	Gate Threshold Voltage	$V_{GE} = V_{CE}$, $I_C = 1.5 \text{ mA}$		5.0	5.8	6.5	V
I _{GES}	Gate – Emitter Leakage Current	$V_{GE} = 20V, V_{CE} = 0V$				400	nA

Dynamic Characteristics

Symbol	Characteristic	Test Conditions		Тур	Max	Unit
Cies	Input Capacitance	$V_{GE} = 0V$		9200		
Coes	Output Capacitance	$V_{CE} = 25V$		580		pF
C _{res}	Reverse Transfer Capacitance	f=1MHz		270		
T _{d(on)}	Turn-on Delay Time	Inductive Switching (25°C)		115		
T _r	Rise Time	$V_{GE} = \pm 15V$		45		
T _{d(off)}	Turn-off Delay Time	$V_{Bus} = 300V$ $I_{C} = 150A$		225		ns
$T_{\rm f}$	Fall Time	$R_G = 3.3\Omega$		55		
T _{d(on)}	Turn-on Delay Time	Inductive Switching (150°C)		130		
T _r	Rise Time	$V_{GE} = \pm 15V$ $V_{Bus} = 300V$		50		ns
T _{d(off)}	Turn-off Delay Time	$I_{\rm C} = 150 {\rm A}$		300		115
T _f	Fall Time	$R_G = 3.3\Omega$		70		
Eon	Turn on Energy	$V_{GE} = \pm 15V$ $T_j = 25^{\circ}C$		0.85		mJ
Lon	Turn on Energy	$V_{Bus} = 300V$ $T_j = 150^{\circ}C$		1.5		1113
Б	Turn off Energy	$I_{\rm C} = 150 {\rm A}$ $T_{\rm j} = 25^{\circ} {\rm C}$		4.1		mJ
E _{off}	Turn off Energy	$R_G = 3.3\Omega$ $T_j = 150^{\circ}C$		5.3		1113

Reverse diode ratings and characteristics

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
V _{RRM}	Maximum Peak Repetitive Reverse Voltage			600			V
I _{RM}	Maximum Reverse Leakage Current	$V_{R}=600V$ $I_{F}=150A$ $V_{GE}=0V$	$T_i = 25^{\circ}C$ $T_i = 150^{\circ}C$			250 500	μΑ
I _F	DC Forward Current		$T_c = 80^{\circ}C$		150	500	А
$V_{\rm F}$	Diode Forward Voltage		$T_i = 25^{\circ}C$		1.6	2	V
v F	Diode Forward Voltage		$T_{i} = 150^{\circ}C$		1.5		v
t	Reverse Recovery Time		$T_j = 25^{\circ}C$		130		ns
t _{rr}	Reverse Recovery Time		$T_{j} = 150^{\circ}C$		225		115
0	Reverse Recovery Charge $I_F = 150A$ $V_R = 300V$ $di/dt = 3000A/\mu s$		$T_j = 25^{\circ}C$		6.9		чС
Q _{rr}				$T_{i} = 150^{\circ}C$		14.5	
Б	Pavaraa Paaayary Enargy	1	$T_j = 25^{\circ}C$		1.6		mI
Er	Reverse Recovery Energy		$T_{j} = 150^{\circ}C$		3.5		mJ



APTGT150H60TG

Temperature sensor NTC (see application note APT0406 on www.microsemi.com for more information).

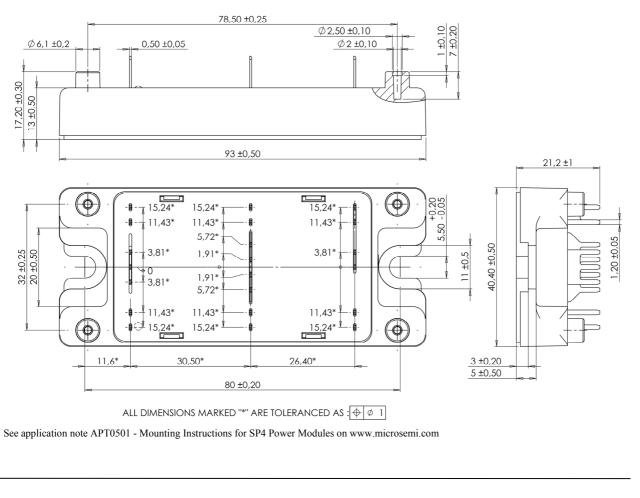
Symbol	Characteristic	Min	Тур	Max	Unit
R ₂₅	Resistance @ 25°C		50		kΩ
B 25/85	$T_{25} = 298.15 \text{ K}$		3952		K
-	$R_{-} = \frac{R_{25}}{1}$ T: Thermistor temperature				

$$R_{T} = \frac{R_{25}}{\exp\left[B_{25/85}\left(\frac{1}{T_{25}} - \frac{1}{T}\right)\right]}$$
 T: Thermistor temperature
R_T: Thermistor value at T

Thermal and package characteristics

Symbol	Characteristic		Min	Тур	Max	Unit	
R _{thJC}	Junction to Case Thermal Resistance		IGBT			0.31	°C/W
R _{th} JC	sunction to Case Therman Resistance		Diode			0.52	C/W
V _{ISOL}	RMS Isolation Voltage, any terminal to case t =1 min, 50/60Hz		4000			V	
T _J	Operating junction temperature range		-40		175		
T _{STG}	Storage Temperature Range		-40		125	°C	
T _C	Operating Case Temperature		-40		100		
Torque	Mounting torque	To Heatsink	M5	2.5		4.7	N.m
Wt	Package Weight				160	g	

SP4 Package outline (dimensions in mm)

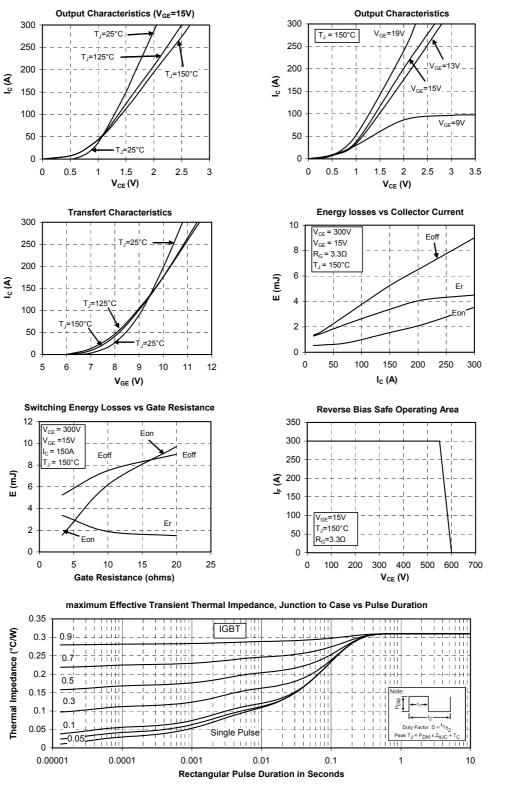


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Typical Performance Curve

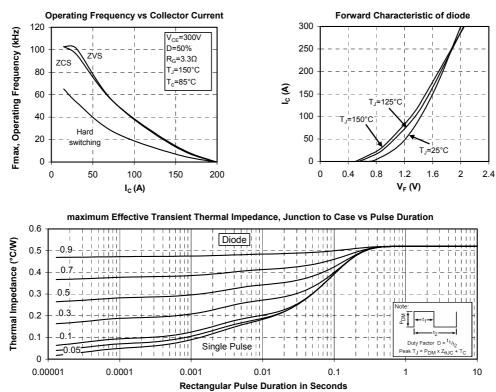
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